

**AO4437**
**P-Channel Enhancement Mode Field Effect Transistor**

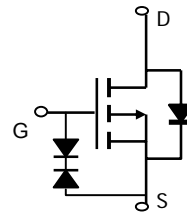
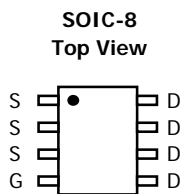
**General Description**

The AO4437 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

*Standard Product AO4437 is Pb-free (meets ROHS & Sony 259 specifications). AO4437L is a Green Product ordering option. AO4437 and AO4437L are electrically identical.*

**Features**

$V_{DS}$  (V) = -12V  
 $I_D$  = -11 A ( $V_{GS}$  = -4.5V)  
 $R_{DS(ON)} < 16m\Omega$  ( $V_{GS}$  = -4.5V)  
 $R_{DS(ON)} < 20m\Omega$  ( $V_{GS}$  = -2.5V)  
 $R_{DS(ON)} < 25m\Omega$  ( $V_{GS}$  = -1.8V)  
 ESD Rating: 4KV HBM


**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-12	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ\text{C}$	-11	A
	$T_A=70^\circ\text{C}$	-9	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-20	
Power Dissipation <sup>A</sup>	$T_A=25^\circ\text{C}$	3	W
	$T_A=70^\circ\text{C}$	2.1	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units	
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	$t \leq 10\text{s}$	31	40	$^\circ\text{C/W}$
		Steady-State	63	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	21	30	$^\circ\text{C/W}$	

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-12			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-9.6\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 4.5\text{V}$			$\pm 1$	$\mu\text{A}$
		$V_{DS}=0\text{V}, V_{GS}=\pm 8\text{V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.3	-0.55	-1	
$I_{D(ON)}$	On state drain current	$V_{GS}=-4.5\text{V}, V_{DS}=-5\text{V}$	-20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-4.5\text{V}, I_D=-11\text{A}$ $T_J=125^\circ\text{C}$		12.4 17	16 21	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}, I_D=-10\text{A}$		15.9	20	$\text{m}\Omega$
		$V_{GS}=-1.8\text{V}, I_D=-6\text{A}$		20.4	25	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-11\text{A}$		38		S
$V_{SD}$	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.74	-1	V
$I_S$	Maximum Body-Diode Continuous Current				-4.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-6\text{V}, f=1\text{MHz}$		3960	4750	pF
$C_{oss}$	Output Capacitance			910		pF
$C_{rss}$	Reverse Transfer Capacitance			757		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		6.9	8.5	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=-4.5\text{V}, V_{DS}=-6\text{V}, I_D=-11\text{A}$		37	47	nC
$Q_{gs}$	Gate Source Charge			4.5		nC
$Q_{gd}$	Gate Drain Charge			11		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=-4.5\text{V}, V_{DS}=-6\text{V}, R_L=0.55\Omega,$ $R_{GEN}=3\Omega$		15		ns
$t_r$	Turn-On Rise Time			43		ns
$t_{D(off)}$	Turn-Off Delay Time			158		ns
$t_f$	Turn-Off Fall Time			95		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=-11\text{A}, di/dt=100\text{A}/\mu\text{s}$		64		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=-11\text{A}, di/dt=100\text{A}/\mu\text{s}$		50		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $\leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

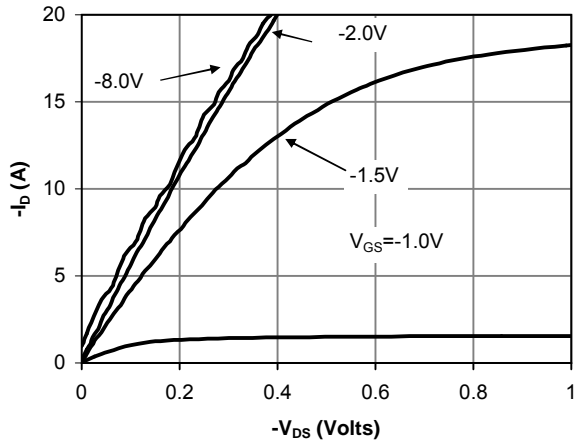


Fig 1: On-Region Characteristics

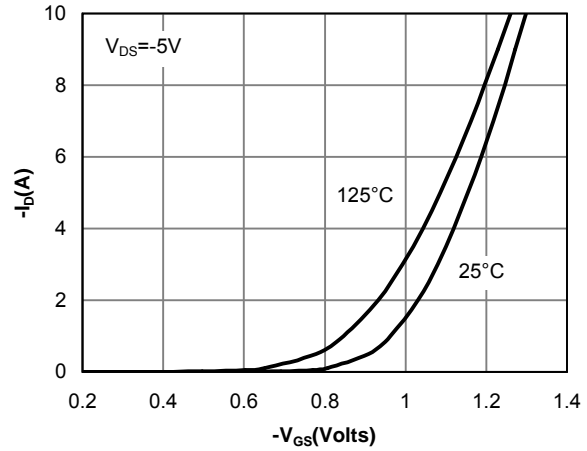


Figure 2: Transfer Characteristics

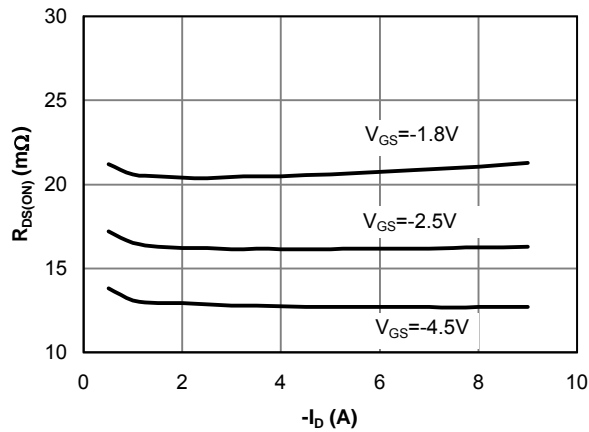


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

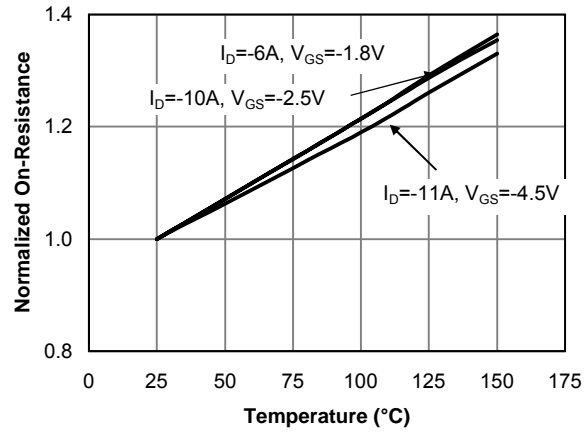


Figure 4: On-Resistance vs. Junction Temperature

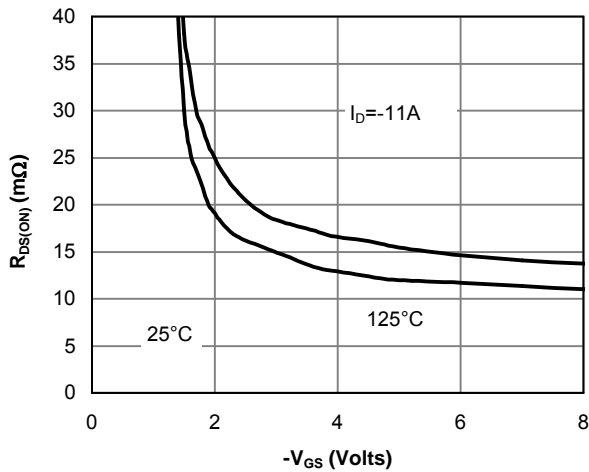


Figure 5: On-Resistance vs. Gate-Source Voltage

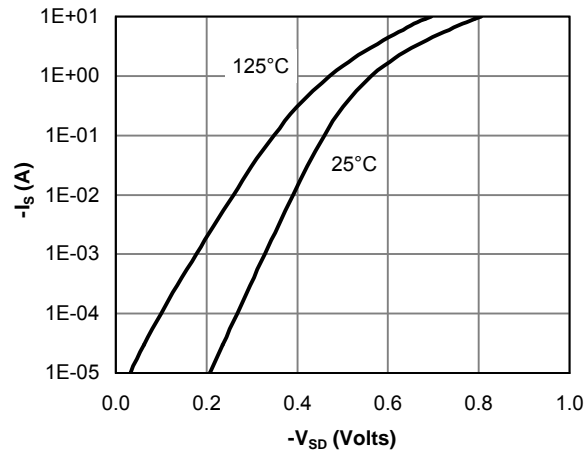


Figure 6: Body-Diode Characteristics

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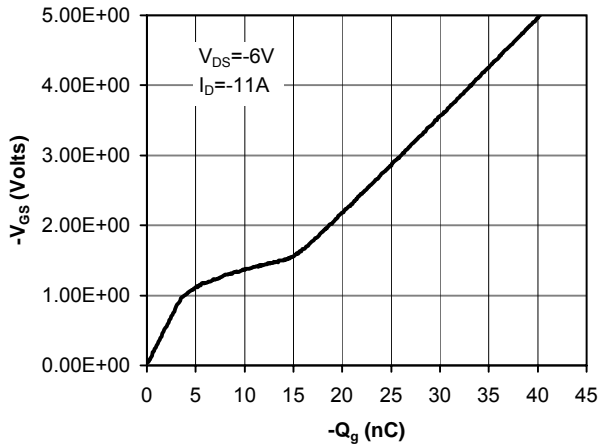


Figure 7: Gate-Charge Characteristics

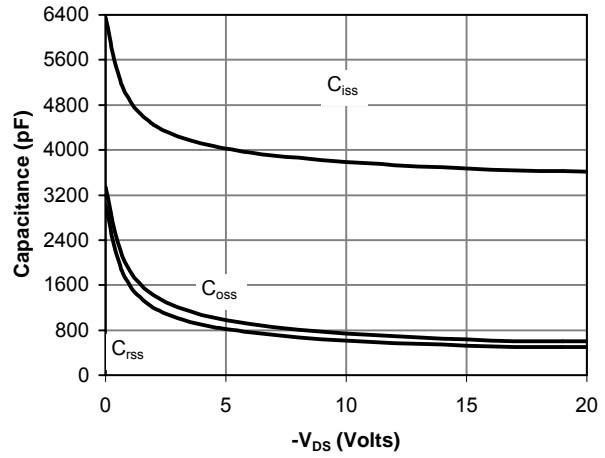


Figure 8: Capacitance Characteristics

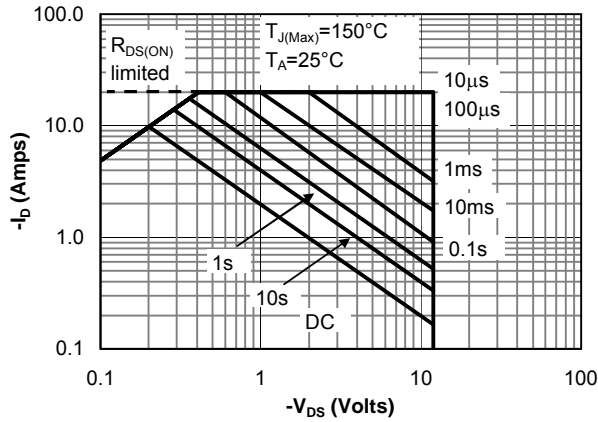


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

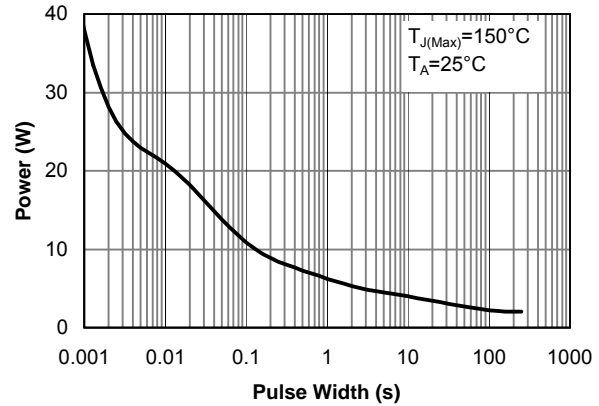


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

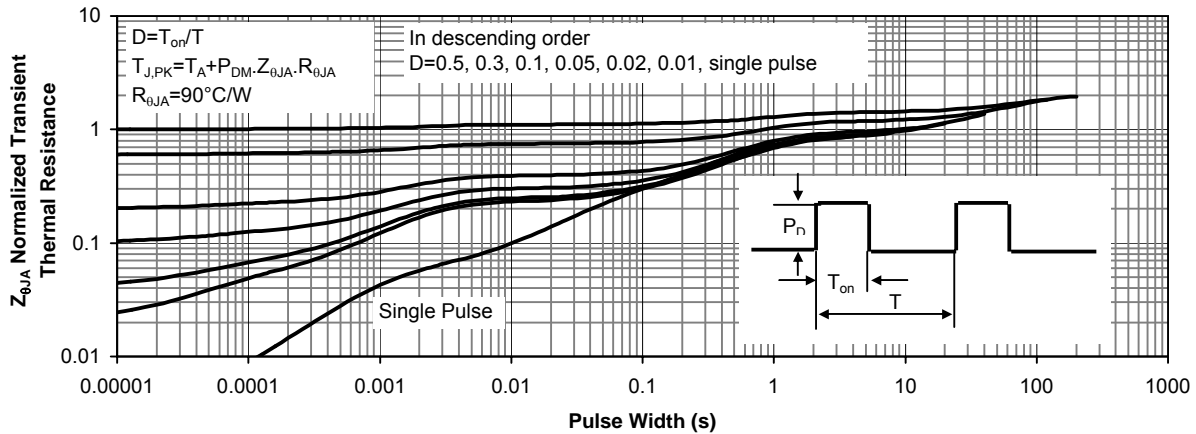


Figure 11: Normalized Maximum Transient Thermal Impedance